

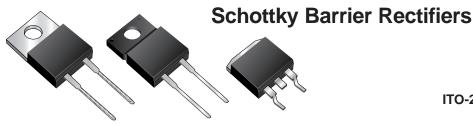


### MBR16Hxx, MBRF16Hxx & MBRB16Hxx Series

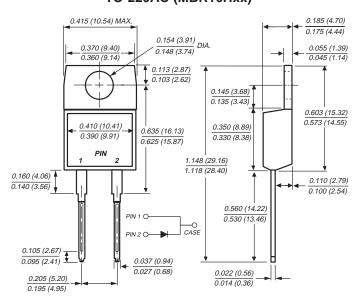
**New Product** 

Vishay Semiconductors formerly General Semiconductor

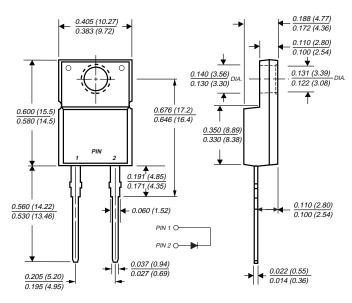
> Reverse Voltage 35 to 60 V Forward Current 16 A



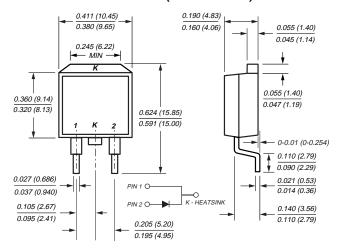
### TO-220AC (MBR16Hxx)



### ITO-220AC (MBRF16Hxx)



#### TO-263AB (MBRB16Hxx)



### **Mechanical Data**

Case: JEDEC TO-220AC, ITO-220AC & TO-263AB molded

plastic body

Terminals: Plated leads, solderable per

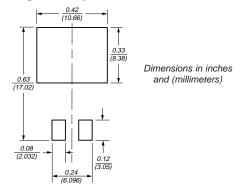
MIL-STD-750, Method 2026

Polarity: As marked Mounting Position: Any

Mounting Torque: 10 in-lbs maximum

Weight: 0.08 oz., 2.24 g

### **Mounting Pad Layout TO-263AB**



#### **Features**

- Plastic package has Underwriters Laboratory Flammability Classification 94 V-0
- Metal silicon junction, majority carrier conduction
- · Low forward voltage drop, low power loss and high efficiency
- Guardring for overvoltage protection
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications
- High temperature soldering guaranteed: 250 °C/10 seconds, 0.25" (6.35 mm) from case
- · Rated for reverse surge and ESD
- 175 °C maximum operation junction temperature

## MBR16Hxx, MBRF16Hxx & MBRB16Hxx Series

## Vishay Semiconductors

formerly General Semiconductor



### Maximum Ratings (T<sub>C</sub> = 25 °C unless otherwise noted)

| Parameter   | Symbol | MBR16H35  | MBR16H45 | MBR16H50 | MBR16H60 | Unit |
|---|--------|---|----------|----------|----------|------|
| Maximum repetitive peak reverse voltage   | VRRM   | 35  | 45       | 50       | 60       | V    |
| Working peak reverse voltage  | VRWM   | 35  | 45       | 50       | 60       | V    |
| Maximum DC blocking voltage   | VDC    | 35  | 45       | 50       | 60       | V    |
| Max. average forward rectified current (see fig. 1)   | IF(AV) | 16  |          |          |          | Α    |
| Peak repetitive forward current at Tc = 150 °C (rated VR, 20 KHz sq. wave)                                | IFRM   | 32  |          |          |          | А    |
| Non-repetitive avalanche energy at 25 °C, I <sub>AS</sub> = 4 A, L = 10 mH                                | Eas    | 80  |          |          | mJ       |      |
| Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load (JEDEC Method)         | IFSM   | 150   |          |          | А        |      |
| Peak repetitive reverse surge current at $t_p = 2.0 \mu s$ , 1 KHz  | IRRM   | 1.0 0.5   |          | .5       | А        |      |
| Peak non-repetitive reverse energy (8/20 µs waveform)   | ERSM   | 20  |          |          | mJ       |      |
| Electrostatic discharge capacitor voltage Human body model: $C = 100 \text{ pF}, R = 1.5 \text{ k}\Omega$ | Vc     | 25  |          |          | kV       |      |
| Voltage rate of change (rated V <sub>R</sub> )  | dv/dt  | 10,000  |          |          | V/μs     |      |
| Operating junction temperature range  | TJ     | -65 to +175   |          |          | °C       |      |
| Storage temperature range   | Tstg   | -65 to +175   |          |          |          | °C   |
| RMS Isolation voltage (MBRF type only) from terminals to heatsink with t = 1.0 second, RH $\leq$ 30%      | Visol  | 4500 <sup>(1)</sup><br>3500 <sup>(2)</sup><br>1500 <sup>(3)</sup> |          |          | V        |      |

### Electrical Characteristics (Tc = 25 °C unless otherwise noted)

| Parameter  |                              | Symbol  | MBR16H35, MBR16H45 |           | MBR16H50, MBR16H60 |           | Unit         |          |
|--|------------------------------|---|--------------------|-----------|--------------------|-----------|--------------|----------|
|  |                              |   | Тур                | Max       | Тур                | Max       | Offic        |          |
| Maximum instantaneous forward voltage <sup>(4)</sup> | at IF = 16 A<br>at IF = 16 A | T <sub>J</sub> = 25 °C<br>T <sub>J</sub> = 125 °C | VF                 | _<br>0.52 | 0.66<br>0.56       | _<br>0.58 | 0.73<br>0.62 | V        |
| (4)  |                              | T <sub>J</sub> = 25 °C<br>T <sub>J</sub> =125 °C  | IR                 | -<br>6.0  | 100<br>20          | -<br>4.0  | 100<br>20    | μA<br>mA |

### Thermal Characteristics (TC = 25°C unless otherwise noted)

| Parameter  | Symbol | MBR | MBRF | MBRB | Unit |
|--|--------|-----|------|------|------|
| Typical thermal resistance from junction to case | Rejc   | 1.5 | 3.0  | 1.5  | °C/W |

(1) Clip mounting (on case), where lead does not overlap heatsink with 0.110" offset  $\,$ (2) Clip mounting (on case), where leads do overlap heatsink

- (3) Screw mounting with 4-40 screw, where washer diameter is  $\leq$  4.9 mm (0.19")
- (4) Pulse test: 300 µs pulse width, 1% duty cycle

### **Ordering Information**

| Product               | Case      | Package Code   | Package Option   |
|-----------------------|-----------|----------------|--|
| MBR16H35 – MBR16H60   | TO-220AC  | 45             | Anti-Static tube, 50/tube, 2K/carton   |
| MBRF16H35 – MBRF16H60 | ITO-220AC | 45             | Anti-Static tube, 50/tube, 2K/carton   |
| MBRB16H35 – MBRB16H60 | TO-263AB  | 31<br>45<br>81 | 13" reel, 800/reel, 4.8K/carton<br>Anti-Static tube, 50/tube, 2K/carton<br>Anti-Static 13" reel, 800/reel, 4.8K/carton |

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# Ratings and Characteristic Curves (TA = 25°C unless otherwise noted)

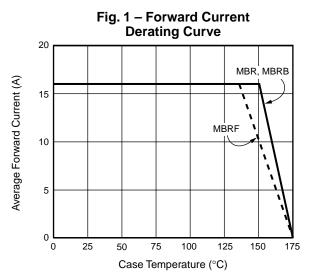


Fig. 3 – Typical Instantaneous Forward Characteristics

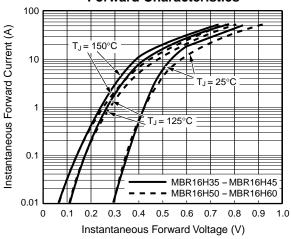


Fig. 5 – Typical Junction Capacitance

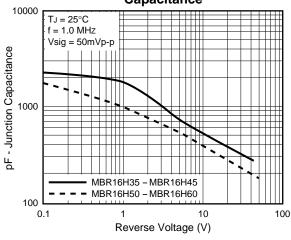


Fig. 2 – Maximum Non-Repetitive Peak Forward Surge Current

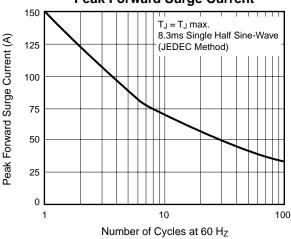
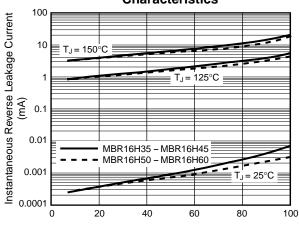


Fig. 4 – Typical Reverse Characteristics



Percent of Rated Peak Reverse Voltage (%)

